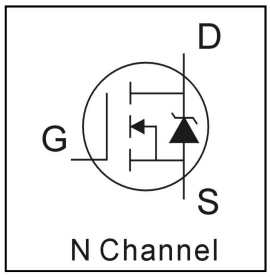
Gunter Semiconductor GmbH | GFC110

N Channel Power MOSFET with low $R_{DS(on)}$



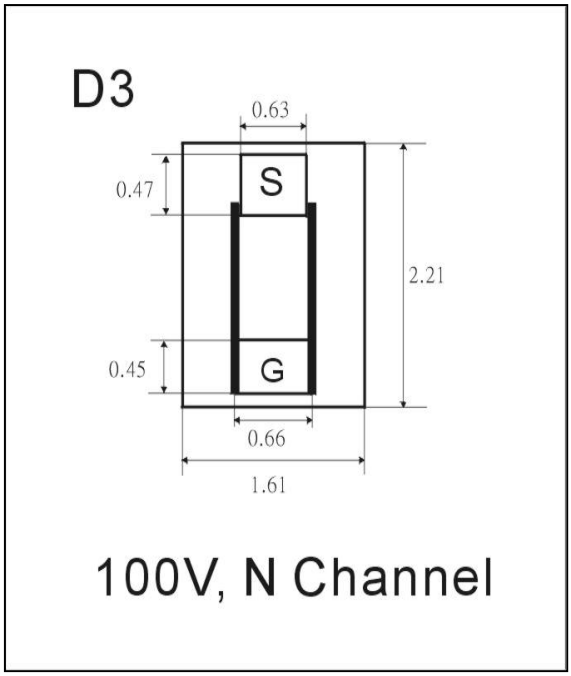
Chip Specification

General Description:

* Advanced Process Technology
* Dynamic dV/dt Rating
* **175℃ Operating Temperature**
* **Fast Switching**
* **Fully Avalanche Rated**
* **Low $R_{DS(on)}$**

Mechanical Data:

D3	
Dimension	**1.61mm x 2.21mm**
Thickness:	**400 μm**
Metallization**:**	
Top :	: **Al**
Backside :	**CrNiAg / Au**
Suggested Bonding Conditions:	
Die Mounting:	**Solder Perform**
95/5 PbSn or 92.5./2.5/5 PbAgIn	
Source Bonding Wire**:**	**5 mil Al**



Absolute Maximum Rating **@Ta=25℃**

Characteristics	Symbol	Limit	Unit	Test Conditions
Drain-to-Source Breakdown Voltage	V(BR)DSS	100	V	VGS=0V, ID=250μA
Static Drain-to - Source On-resistance	RDS(ON)	0.54	Ω	VGS=10V, ID=3.4A
Continuous Drain current (in target package)	ID@25℃	5.6	A	VGS=10V
Continuous Drain current (in target package)	ID@100℃	4	A	VGS=10V
Operation Junction	Tj	-55~175	℃	
Storage Temperature	TSTR	-55~175	℃	

Target Device: IRF510

TO-220AB	P_D	43	W	@Tc=25℃